

Crystal Properties			
PARAMETER	UNITS	SPECIFICATION	NOTE
Crystalline structure	-	Monocrystalline	
Growth technique	-	Czochralski (Cz)	
Orientation	-	<100> ±1°	
Slice orientation	Degrees	ON ±1.0°	
Electrical Properties			
PARAMETER	UNITS	SPECIFICATION	NOTE
Conductance type	-	P-type	
Dopant	-	Boron	
Resistivity	Ω-cm	Any	
Geometrical Properties			
PARAMETER	UNITS	SPECIFICATION	NOTE
Diameter	mm	300±0.10	
Thickness	μm	775±25	
Notch	-	SEMI Standard	
Notch depth	mm	1.0 + 0.25 – 0.00	
Notch angle	-	90° +5° -1°	
Notch orientation	-	<110>±1°	
Surface Appearance			
PARAMETER	UNITS	SPECIFICATION	NOTE
Front surface	-	Polished	
Back surface	-	Polished	
Frontside particles ≥0.20 μm (LPD/COP)	No./wafer	≤200	
Wafer Identification			
PARAMETER	UNITS	SPECIFICATION	NOTE
Lasermark	-	SEMI Standard Backside T7 and M12	